### TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# SM8LZ47

#### AC POWER CONTROL APPLICATIONS

• Repetitive Peak Off–State Voltage  $: V_{DRM} = 800V$ • R.M.S ON–State Current  $: I_{T(RMS)} = 8A$ 

• High Commutating (dv / dt) :  $(dv / dt) c = 10V / \mu s$  (Min.)

• Isolation Voltage  $: V_{ISOL} = 1500 V AC$ 

#### **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive PeakOff-State Voltage	$V_{DRM}$	800	V	
R.M.S On-State Current (Full Sine Waveform)	I <sub>T (RMS)</sub>	8	Α	
Peak One Cycle Surge On-State	I	70 (50Hz)	Α	
Current (Non-Repetitive)	ITSM	80 (60Hz)	A	
I <sup>2</sup> t Limit Value	I <sup>2</sup> t	24.5	A <sup>2</sup> s	
Critical Rate of Rise of On-State Current (Note 1)	di / dt	50	A / μs	
Peak Gate Power Dissipation	$P_{GM}$	5	W	
Average Gate Power Dissipation	P <sub>G (AV)</sub>	0.5	W	
Peak Gate Voltage	$V_{FGM}$	10	V	
Peak Gate Current	I <sub>GM</sub>	2	Α	
Junction Temperature	Tj	-40~125	°C	
Storage Temperature Range	T <sub>stg</sub>	-40~125	°C	
Isolation Voltage (AC, t = 1min.)	V <sub>ISOL</sub>	1500	V	

Weight: 1.7g

Note: di / dt test condition

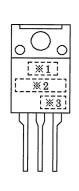
 $V_{DRM} = 400V, \ I_{TM} \leq 12A, \ t_{gw} \geq 10\mu s, \ t_{gr} \leq 250ns,$ 

 $i_{gp} = I_{GT} \times 2.0$ 

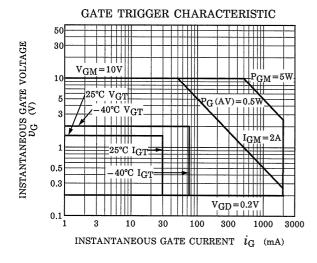
# **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

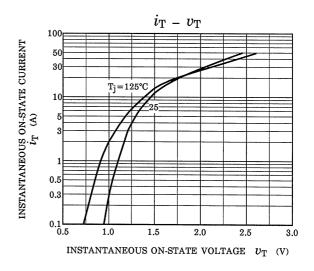
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT
Repetitive Peak Off-State Current		I <sub>DRM</sub>	V <sub>DRM</sub> = 800V		_	_	20	μA
Gate Trigger Voltage	I		V <sub>D</sub> = 12V R <sub>L</sub> = 20Ω	T2 (+), Gate (+)	_	_	1.5	V
	II	$V_{GT}$		T2 (+), Gate (-)	_	_	1.5	
	III			T2 (-), Gate (-)	_	_	1.5	
Gate Trigger Current	I	I <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 20Ω	T2 (+), Gate (+)	_	_	30	mA
	II			T2 (+), Gate (-)	_	_	30	
	III			T2 (-), Gate (-)	_	_	30	
Peak On-State Voltage		V <sub>TM</sub>	I <sub>TM</sub> = 12A		_	_	1.5	V
Gate Non-Trigger Voltage V <sub>GD</sub>		$V_{GD}$	V <sub>D</sub> = 800V, Tc = 125°C		0.2	_	_	V
Holding Current		lн	V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A		_	_	50	mA
Thermal Resistance		R <sub>th (j−c)</sub>	Junction to Case, AC		_	_	3.6	°C/W
Critical Rate of Rise of Off- State Voltage		dv / dt	V <sub>DRM</sub> = 800V, T <sub>j</sub> = 125°C Exponential Rise		_	300	_	V / µs
Critical Rate of Rise of Off- State Voltage at Commutation		(dv / dt) c	V <sub>DRM</sub> = 400V, T <sub>j</sub> = 125°C (di / dt) c = -4.5Å / ms		10	_	_	V / µs

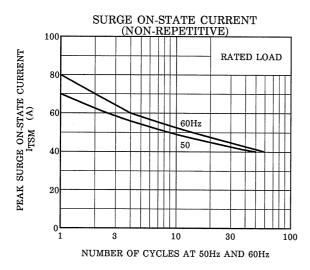
# **MARKING**

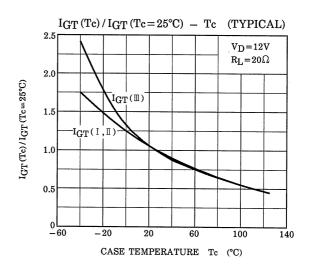


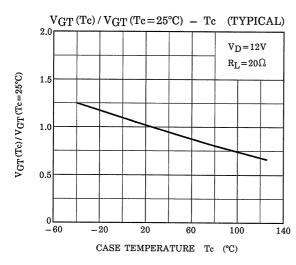
NUMBER		MARK		
* 1	TOSHIBA PRODUCT MARK		7	
* 2	TYPE	SM8LZ47	M8LZ47	
* 3		(Starting from Alphabet A)  Last Decimal Digit of the Current Year	Example  8A: January 1998  8B: Febrary 1998  8L: December 1998	

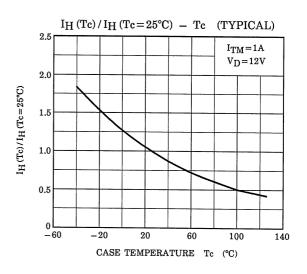




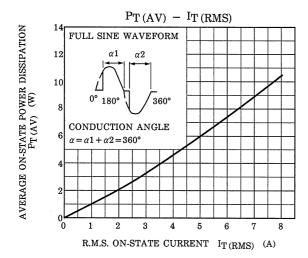


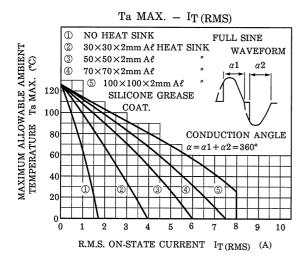


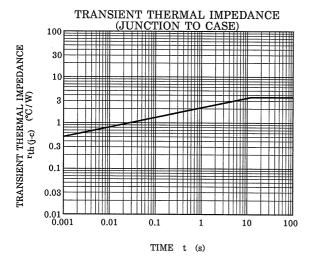


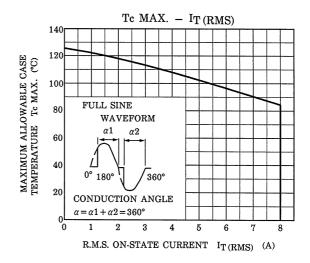


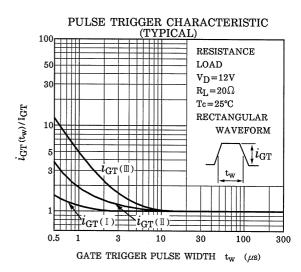
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